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Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of **Embedded - Microprocessors**

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details

Product Status	Obsolete
Core Processor	PowerPC e500
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	1.333GHz
Co-Processors/DSP	Signal Processing; SPE, Security; SEC
RAM Controllers	DDR, DDR2, SDRAM
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (4)
SATA	-
USB	-
Voltage - I/O	1.8V, 2.5V, 3.3V
Operating Temperature	0°C ~ 105°C (TA)
Security Features	Cryptography, Random Number Generator
Package / Case	783-BBGA, FCBGA
Supplier Device Package	783-FCBGA (29x29)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/kmpc8548ehxauj

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

Overview



Figure 1. Device Block Diagram

1.1 Key Features

The following list provides an overview of the device feature set:

- High-performance 32-bit core built on Power Architecture® technology.
 - 32-Kbyte L1 instruction cache and 32-Kbyte L1 data cache with parity protection. Caches can be locked entirely or on a per-line basis, with separate locking for instructions and data.
 - Signal-processing engine (SPE) APU (auxiliary processing unit). Provides an extensive instruction set for vector (64-bit) integer and fractional operations. These instructions use both the upper and lower words of the 64-bit GPRs as they are defined by the SPE APU.
 - Double-precision floating-point APU. Provides an instruction set for double-precision (64-bit) floating-point instructions that use the 64-bit GPRs.
 - 36-bit real addressing
 - Embedded vector and scalar single-precision floating-point APUs. Provide an instruction set for single-precision (32-bit) floating-point instructions.
 - Memory management unit (MMU). Especially designed for embedded applications. Supports 4-Kbyte to 4-Gbyte page sizes.
 - Enhanced hardware and software debug support

Overview

- AESU-Advanced Encryption Standard unit
 - Implements the Rijndael symmetric key cipher
 - ECB, CBC, CTR, and CCM modes
 - 128-, 192-, and 256-bit key lengths
- AFEU—ARC four execution unit
 - Implements a stream cipher compatible with the RC4 algorithm
 - 40- to 128-bit programmable key
- MDEU—message digest execution unit
 - SHA with 160- or 256-bit message digest
 - MD5 with 128-bit message digest
 - HMAC with either algorithm
- KEU—Kasumi execution unit
 - Implements F8 algorithm for encryption and F9 algorithm for integrity checking
 - Also supports A5/3 and GEA-3 algorithms
- RNG—random number generator
- XOR engine for parity checking in RAID storage applications
- Dual I²C controllers
 - Two-wire interface
 - Multiple master support
 - Master or slave I^2C mode support
 - On-chip digital filtering rejects spikes on the bus
- Boot sequencer
 - Optionally loads configuration data from serial ROM at reset via the I^2C interface
 - Can be used to initialize configuration registers and/or memory
 - Supports extended I²C addressing mode
 - Data integrity checked with preamble signature and CRC
- DUART
 - Two 4-wire interfaces (SIN, SOUT, $\overline{\text{RTS}}$, $\overline{\text{CTS}}$)
 - Programming model compatible with the original 16450 UART and the PC16550D
- Local bus controller (LBC)
 - Multiplexed 32-bit address and data bus operating at up to 133 MHz
 - Eight chip selects support eight external slaves
 - Up to eight-beat burst transfers
 - The 32-, 16-, and 8-bit port sizes are controlled by an on-chip memory controller.
 - Three protocol engines available on a per chip select basis:
 - General-purpose chip select machine (GPCM)
 - Three user programmable machines (UPMs)

5 **RESET** Initialization

This section describes the AC electrical specifications for the RESET initialization timing requirements of the device. The following table provides the RESET initialization AC timing specifications for the DDR SDRAM component(s).

Parameter/Condition	Min	Мах	Unit	Notes
Required assertion time of HRESET	100	—	μS	—
Minimum assertion time for SRESET	3	—	SYSCLKs	1
PLL input setup time with stable SYSCLK before HRESET negation	100	—	μS	—
Input setup time for POR configs (other than PLL config) with respect to negation of HRESET	4	—	SYSCLKs	1
Input hold time for all POR configs (including PLL config) with respect to negation of HRESET	2	—	SYSCLKs	1
Maximum valid-to-high impedance time for actively driven POR configs with respect to negation of HRESET	—	5	SYSCLKs	1

Table 8. RESE1	Initialization	Timing	Specifications
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Note:

1. SYSCLK is the primary clock input for the device.

The following table provides the PLL lock times.

Table 9. PLL Lock Times

Parameter/Condition	Min	Мах	Unit
Core and platform PLL lock times	—	100	μS
Local bus PLL lock time	—	50	μS
PCI/PCI-X bus PLL lock time	—	50	μS

5.1 Power-On Ramp Rate

This section describes the AC electrical specifications for the power-on ramp rate requirements.

Controlling the maximum power-on ramp rate is required to avoid falsely triggering the ESD circuitry. The following table provides the power supply ramp rate specifications.

Table 10.	Power	Supply	Ramp	Rate
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Parameter	Min	Мах	Unit	Notes
Required ramp rate for MVREF	—	3500	V/s	1
Required ramp rate for VDD	_	4000	V/s	1, 2

Note:

1. Maximum ramp rate from 200 to 500 mV is most critical as this range may falsely trigger the ESD circuitry.

2. VDD itself is not vulnerable to false ESD triggering; however, as per Section 22.2, "PLL Power Supply Filtering," the recommended AVDD_CORE, AVDD_PLAT, AVDD_LBIU, AVDD_PCI1 and AVDD_PCI2 filters are all connected to VDD. Their ramp rates must be equal to or less than the VDD ramp rate.

6 DDR and DDR2 SDRAM

This section describes the DC and AC electrical specifications for the DDR SDRAM interface of the device. Note that $GV_{DD}(typ) = 2.5 \text{ V}$ for DDR SDRAM, and $GV_{DD}(typ) = 1.8 \text{ V}$ for DDR2 SDRAM.

6.1 DDR SDRAM DC Electrical Characteristics

The following table provides the recommended operating conditions for the DDR2 SDRAM controller of the device when $GV_{DD}(typ) = 1.8 \text{ V}.$

Parameter/Condition	Symbol	Min	Max	Unit	Notes
I/O supply voltage	GV _{DD}	1.71	1.89	V	1
I/O reference voltage	MV _{REF}	$0.49 \times GV_{DD}$	$0.51 \times GV_{DD}$	V	2
I/O termination voltage	V _{TT}	MV _{REF} – 0.04	MV _{REF} + 0.04	V	3
Input high voltage	V _{IH}	MV _{REF} + 0.125	GV _{DD} + 0.3	V	—
Input low voltage	V _{IL}	-0.3	MV _{REF} – 0.125	V	—
Output leakage current	I _{OZ}	-50	50	μA	4
Output high current (V _{OUT} = 1.420 V)	I _{ОН}	-13.4	—	mA	—
Output low current (V _{OUT} = 0.280 V)	I _{OL}	13.4	—	mA	—

Table 11. DDR2 SDRAM DC Electrical Characteristics for GV_{DD}(typ) = 1.8 V

Notes:

1. GV_{DD} is expected to be within 50 mV of the DRAM V_{DD} at all times.

2. MV_{REF} is expected to be equal to 0.5 × GV_{DD} , and to track GV_{DD} DC variations as measured at the receiver. Peak-to-peak noise on MV_{REF} may not exceed ±2% of the DC value.

3. V_{TT} is not applied directly to the device. It is the supply to which far end signal termination is made and is expected to be equal to MV_{REF}. This rail must track variations in the DC level of MV_{REF}.

4. Output leakage is measured with all outputs disabled, $0 V \le V_{OUT} \le GV_{DD}$.

This table provides the DDR2 I/O capacitance when $GV_{DD}(typ) = 1.8$ V.

Table 12. DDR2 SDRAM Capacitance for GV_{DD}(typ)=1.8 V

Parameter/Condition	Symbol	Min	Мах	Unit	Notes
Input/output capacitance: DQ, DQS, DQS	C _{IO}	6	8	pF	1
Delta input/output capacitance: DQ, DQS, DQS	C _{DIO}	—	0.5	pF	1

Note:

1. This parameter is sampled. $GV_{DD} = 1.8 \text{ V} \pm 0.090 \text{ V}$, f = 1 MHz, T_A = 25°C, $V_{OUT} = GV_{DD}/2$, V_{OUT} (peak-to-peak) = 0.2 V.

6.2.2 DDR SDRAM Output AC Timing Specifications

Table 19. DDR SDRAM Output AC Timing Specifications

At recommended operating conditions.

Parameter	Symbol ¹	Min	Мах	Unit	Notes
MCK[n] cycle time, MCK[<i>n</i>]/MCK[<i>n</i>] crossing	t _{MCK}	3.75	6	ns	2
ADDR/CMD output setup with respect to MCK 533 MHz 400 MHz 333 MHz	t _{ddkhas}	1.48 1.95 2.40		ns	3
ADDR/CMD output hold with respect to MCK 533 MHz 400 MHz 333 MHz	^t ddkhax	1.48 1.95 2.40		ns	3
MCS[<i>n</i>] output setup with respect to MCK 533 MHz 400 MHz 333 MHz	^t DDKHCS	1.48 1.95 2.40		ns	3
MCS[<i>n</i>] output hold with respect to MCK 533 MHz 400 MHz 333 MHz	^t DDKHCX	1.48 1.95 2.40		ns	3
MCK to MDQS Skew	t _{DDKHMH}	-0.6	0.6	ns	4
MDQ/MECC/MDM output setup with respect to MDQS 533 MHz 400 MHz 333 MHz	^t DDKHDS, ^t DDKLDS	538 700 900	 	ps	5
MDQ/MECC/MDM output hold with respect to MDQS 533 MHz 400 MHz 333 MHz	^t ddkhdx, ^t ddkldx	538 700 900		ps	5
MDQS preamble start	t _{DDKHMP}	$-0.5\times t_{MCK}-0.6$	$-0.5 \times t_{\text{MCK}} + 0.6$	ns	6

Enhanced Three-Speed Ethernet (eTSEC)

Figure 15 shows the TBI receive AC timing diagram.



Figure 15. TBI Receive AC Timing Diagram

8.2.5 TBI Single-Clock Mode AC Specifications

When the eTSEC is configured for TBI modes, all clocks are supplied from external sources to the relevant eTSEC interface. In single-clock TBI mode, when TBICON[CLKSEL] = 1, a 125-MHz TBI receive clock is supplied on the TSEC n_RX_CLK pin (no receive clock is used on TSEC n_TX_CLK in this mode, whereas for the dual-clock mode this is the PMA1 receive clock). The 125-MHz transmit clock is applied on the TSEC_GTX_CLK125 pin in all TBI modes.

A summary of the single-clock TBI mode AC specifications for receive appears in Table 32.

Parameter/Condition	Symbol	Min	Тур	Мах	Unit
RX_CLK clock period	t _{TRRX}	7.5	8.0	8.5	ns
RX_CLK duty cycle	t _{TRRH/TRRX}	40	50	60	%
RX_CLK peak-to-peak jitter	t _{TRRJ}	_	_	250	ps
Rise time RX_CLK (20%–80%)	t _{TRRR}	_	_	1.0	ns
Fall time RX_CLK (80%–20%)	t _{TRRF}	_	_	1.0	ns
RCG[9:0] setup time to RX_CLK rising edge	t _{TRRDVKH}	2.0	_	—	ns
RCG[9:0] hold time to RX_CLK rising edge	t _{TRRDXKH}	1.0	_	_	ns

A timing diagram for TBI receive appears in Figure 16.



Figure 16. TBI Single-Clock Mode Receive AC Timing Diagram

8.2.6 RGMII and RTBI AC Timing Specifications

This table presents the RGMII and RTBI AC timing specifications.

Parameter/Condition	Symbol ¹	Min	Тур	Max	Unit
Data to clock output skew (at transmitter)	t _{SKRGT} 5	-500 ⁶	0	500 ⁶	ps
Data to clock input skew (at receiver) ²	t _{SKRGT}	1.0	_	2.8	ns
Clock period ³	t _{RGT} 5	7.2	8.0	8.8	ns
Duty cycle for 10BASE-T and 100BASE-TX ^{3, 4}	t _{RGTH} /t _{RGT} 5	45	50	55	%
Rise time (20%–80%)	t _{RGTR} 5	_	_	0.75	ns
Fall time (20%–80%)	t _{RGTF} 5		—	0.75	ns

Table 33. RGMII and RTBI AC Timing Specifications

Notes:

 In general, the clock reference symbol representation for this section is based on the symbols RGT to represent RGMII and RTBI timing. For example, the subscript of t_{RGT} represents the TBI (T) receive (RX) clock. Note also that the notation for rise (R) and fall (F) times follows the clock symbol that is being represented. For symbols representing skews, the subscript is skew (SK) followed by the clock that is being skewed (RGT).

- 2. This implies that PC board design requires clocks to be routed such that an additional trace delay of greater than 1.5 ns is added to the associated clock signal.
- 3. For 10 and 100 Mbps, t_{RGT} scales to 400 ns \pm 40 ns and 40 ns \pm 4 ns, respectively.
- 4. Duty cycle may be stretched/shrunk during speed changes or while transitioning to a received packet's clock domains as long as the minimum duty cycle is not violated and stretching occurs for no more than three t_{RGT} of the lowest speed transitioned between.

5. Guaranteed by characterization.

6. In rev 1.0 silicon, due to errata, t_{SKRGT} is -650 ps (min) and 650 ps (max). See "eTSEC 10" in the device errata document.

10 Local Bus

This section describes the DC and AC electrical specifications for the local bus interface of the device.

10.1 Local Bus DC Electrical Characteristics

This table provides the DC electrical characteristics for the local bus interface operating at $BV_{DD} = 3.3 \text{ V DC}$.

Parameter	Symbol	Min	Мах	Unit
High-level input voltage	V _{IH}	2	BV _{DD} + 0.3	V
Low-level input voltage	V _{IL}	-0.3	0.8	V
Input current ($V_{IN}^{1} = 0 V \text{ or } V_{IN} = BV_{DD}$)	I _{IN}	_	±5	μΑ
High-level output voltage ($BV_{DD} = min, I_{OH} = -2 mA$)	V _{OH}	2.4	—	V
Low-level output voltage (BV_{DD} = min, I_{OL} = 2 mA)	V _{OL}	_	0.4	V

Table 38. Local Bus DC Electrical Characteristics (3.3 V DC)

Note:

1. Note that the symbol V_{IN} , in this case, represents the BV_{IN} symbol referenced in Table 1 and Table 2.

Table 39 provides the DC electrical characteristics for the local bus interface operating at $BV_{DD} = 2.5 \text{ V DC}$.

Table 39. Local Bus DC Electrical Characteristics (2.5 V DC)

Parameter	Symbol	Min	Max	Unit
High-level input voltage	V _{IH}	1.70	BV _{DD} + 0.3	V
Low-level input voltage	V _{IL}	-0.3	0.7	V
Input current $(V_{IN}^{1} = 0 V \text{ or } V_{IN} = BV_{DD})$	I _{IH}	—	10	μA
	IIL		-15	
High-level output voltage ($BV_{DD} = min, I_{OH} = -1 mA$)	V _{OH}	2.0	—	V
Low-level output voltage ($BV_{DD} = min$, $I_{OL} = 1 mA$)	V _{OL}	—	0.4	V

Note:

1. Note that the symbol V_{IN} , in this case, represents the BV_{IN} symbol referenced in Table 1 and Table 2.

Local Bus



Figure 26. Local Bus Signals, GPCM/UPM Signals for LCCR[CLKDIV] = 4 (PLL Bypass Mode)



Figure 27. Local Bus Signals, GPCM/UPM Signals for LCCR[CLKDIV] = 8 or 16 (PLL Enabled)

of a balanced interchange circuit and ground. In this example, for SerDes output, $V_{cm_out} = V_{SD_TX} + V_{\overline{SD}_TX} = (A + B)/2$, which is the arithmetic mean of the two complimentary output voltages within a differential pair. In a system, the common mode voltage may often differ from one component's output to the other's input. Sometimes, it may be even different between the receiver input and driver output circuits within the same component. It is also referred to as the DC offset.



To illustrate these definitions using real values, consider the case of a CML (current mode logic) transmitter that has a common mode voltage of 2.25 V and each of its outputs, TD and TD, has a swing that goes between 2.5 and 2.0 V. Using these values, the peak-to-peak voltage swing of each signal (TD or TD) is 500 mVp-p, which is referred as the single-ended swing for each signal. In this example, since the differential signaling environment is fully symmetrical, the transmitter output's differential swing (V_{OD}) has the same amplitude as each signal's single-ended swing. The differential output signal ranges between 500 and -500 mV, in other words, V_{OD} is 500 mV in one phase and -500 mV in the other phase. The peak differential voltage (V_{DIFFp}) is 500 mV. The peak-to-peak differential voltage (V_{DIFFp}) is 1000 mVp-p.

16.2 SerDes Reference Clocks

The SerDes reference clock inputs are applied to an internal PLL whose output creates the clock used by the corresponding SerDes lanes. The SerDes reference clocks inputs are SD_REF_CLK and SD_REF_CLK for PCI Express and serial RapidIO.

The following sections describe the SerDes reference clock requirements and some application information.

16.2.1 SerDes Reference Clock Receiver Characteristics

Figure 39 shows a receiver reference diagram of the SerDes reference clocks.

- The supply voltage requirements for $XV_{DD SRDS2}$ are specified in Table 1 and Table 2.
- SerDes Reference clock receiver reference circuit structure:

Symbol	Parameter	Min	Nom	Max	Unit	Comments
T _{crosslink}	Crosslink random timeout	0		1	ms	This random timeout helps resolve conflicts in crosslink configuration by eventually resulting in only one downstream and one upstream port. See Note 7.

Notes:

1. No test load is necessarily associated with this value.

- 2. Specified at the measurement point into a timing and voltage compliance test load as shown in Figure 50 and measured over any 250 consecutive TX UIs. (Also see the transmitter compliance eye diagram shown in Figure 48.)
- 3. A T_{TX-EYE} = 0.70 UI provides for a total sum of deterministic and random jitter budget of T_{TX-JITTER-MAX} = 0.30 UI for the transmitter collected over any 250 consecutive TX UIs. The T_{TX-EYE-MEDIAN-to-MAX-JITTER} median is less than half of the total TX jitter budget collected over any 250 consecutive TX UIs. Note that the median is not the same as the mean. The jitter median describes the point in time where the number of jitter points on either side is approximately equal as opposed to the averaged time value.
- 4. The transmitter input impedance shall result in a differential return loss greater than or equal to 12 dB and a common mode return loss greater than or equal to 6 dB over a frequency range of 50 MHz to 1.25 GHz. This input impedance requirement applies to all valid input levels. The reference impedance for return loss measurements is 50 Ω to ground for both the D+ and D- line (that is, as measured by a vector network analyzer with 50- Ω probes—see Figure 50). Note that the series capacitors C_{TX} is optional for the return loss measurement.
- 5. Measured between 20%–80% at transmitter package pins into a test load as shown in Figure 50 for both V_{TX-D+} and V_{TX-D-}.
- 6. See Section 4.3.1.8 of the PCI Express Base Specifications Rev 1.0a.
- 7. See Section 4.2.6.3 of the PCI Express Base Specifications Rev 1.0a.
- 8. MPC8548E SerDes transmitter does not have CTX built in. An external AC coupling capacitor is required.

17.4.2 Transmitter Compliance Eye Diagrams

The TX eye diagram in Figure 48 is specified using the passive compliance/test measurement load (see Figure 50) in place of any real PCI Express interconnect +RX component.

There are two eye diagrams that must be met for the transmitter. Both eye diagrams must be aligned in time using the jitter median to locate the center of the eye diagram. The different eye diagrams differ in voltage depending whether it is a transition bit or a de-emphasized bit. The exact reduced voltage level of the de-emphasized bit is always relative to the transition bit.

The eye diagram must be valid for any 250 consecutive UIs.

A recovered TX UI is calculated over 3500 consecutive unit intervals of sample data. The eye diagram is created using all edges of the 250 consecutive UI in the center of the 3500 UI used for calculating the TX UI.

NOTE

It is recommended that the recovered TX UI is calculated using all edges in the 3500 consecutive UI interval with a fit algorithm using a minimization merit function (for example, least squares and median deviation fits).

Table 71. MPC8548E Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
MWE	E7	0	GV _{DD}	—
MCAS	H7	0	GV _{DD}	_
MRAS	L8	0	GV _{DD}	_
MCKE[0:3]	F10, C10, J11, H11	0	GV _{DD}	11
MCS[0:3]	K8, J8, G8, F8	0	GV _{DD}	_
MCK[0:5]	H9, B15, G2, M9, A14, F1	0	GV _{DD}	—
MCK[0:5]	J9, A15, G1, L9, B14, F2	0	GV _{DD}	—
MODT[0:3]	E6, K6, L7, M7	0	GV _{DD}	—
MDIC[0:1]	A19, B19	I/O	GV _{DD}	36
	Local Bus Controller Interface			•
LAD[0:31]	E27, B20, H19, F25, A20, C19, E28, J23, A25, K22, B28, D27, D19, J22, K20, D28, D25, B25, E22, F22, F21, C25, C22, B23, F20, A23, A22, E19, A21, D21, F19, B21	I/O	BV _{DD}	_
LDP[0:3]	K21, C28, B26, B22	I/O	BV _{DD}	—
LA[27]	H21	0	BV _{DD}	5, 9
LA[28:31]	H20, A27, D26, A28	0	BV _{DD}	5, 7, 9
LCS[0:4]	J25, C20, J24, G26, A26	0	ΒV _{DD}	
LCS5/DMA_DREQ2	D23	I/O	BV _{DD}	1
LCS6/DMA_DACK2	G20	0	BV _{DD}	1
LCS7/DMA_DDONE2	E21	0	BV _{DD}	1
LWE0/LBS0/LSDDQM[0]	G25	0	BV _{DD}	5, 9
LWE1/LBS1/LSDDQM[1]	C23	0	BV _{DD}	5, 9
LWE2/LBS2/LSDDQM[2]	J21	0	BV _{DD}	5, 9
LWE3/LBS3/LSDDQM[3]	A24	0	BV _{DD}	5, 9
LALE	H24	0	BV _{DD}	5, 8, 9
LBCTL	G27	0	BV _{DD}	5, 8, 9
LGPL0/LSDA10	F23	0	BV _{DD}	5, 9
LGPL1/LSDWE	G22	0	BV _{DD}	5, 9
LGPL2/LOE/LSDRAS	B27	0	BV _{DD}	5, 8, 9
LGPL3/LSDCAS	F24	0	BV _{DD}	5, 9
LGPL4/LGTA/LUPWAIT/LPBSE	H23	I/O	BV _{DD}	_
LGPL5	E26	0	BV _{DD}	5, 9
LCKE	E24	0	BV _{DD}	_
LCLK[0:2]	E23, D24, H22	0	BV _{DD}	—

Table 71	. MPC8548E	Pinout Listing	(continued)
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Signal	Package Pin Number	Pin Type	Power Supply	Notes	
	Clock				
RTC	AF16	I	OV _{DD}	—	
SYSCLK	AH17	I	OV _{DD}	—	
	JTAG				
ТСК	AG28	I	OV _{DD}	—	
TDI	AH28	I	OV _{DD}	12	
TDO	AF28	0	OV _{DD}	—	
TMS	AH27	ļ	OV _{DD}	12	
TRST	AH23	I	OV _{DD}	12	
	DFT				
L1_TSTCLK	AC25	I	OV _{DD}	25	
L2_TSTCLK	AE22	I	OV _{DD}	25	
LSSD_MODE	AH20	I	OV _{DD}	25	
TEST_SEL	AH14	I	OV _{DD}	25	
Thermal Management					
THERM0	AG1	—	—	14	
THERM1	AH1	—	_	14	
	Power Management				
ASLEEP	AH18	0	OV _{DD}	9, 19, 29	
	Power and Ground Signals				
GND	 A11, B7, B24, C1, C3, C5, C12, C15, C26, D8, D11, D16, D20, D22, E1, E5, E9, E12, E15, E17, F4, F26, G12, G15, G18, G21, G24, H2, H6, H8, H28, J4, J12, J15, J17, J27, K7, K9, K11, K27, L3, L5, L12, L16, N11, N13, N15, N17, N19, P4, P9, P12, P14, P16, P18, R11, R13, R15, R17, R19, T4, T12, T14, T16, T18, U8, U11, U13, U15, U17, U19, V4, V12, V18, W6, W19, Y4, Y9, Y11, Y19, AA6, AA14, AA17, AA22, AA23, AB4, AC2, AC11, AC19, AC26, AD5, AD9, AD22, AE3, AE14, AF6, AF10, AF13, AG8, AG27, K28, L24, L26, N24, N27, P25, R28, T24, T26, U24, V25, W28, Y24, Y26, AA24, AA27, AB25, AC28, L21, L23, N22, P20, R23, T21, U22, V20, W23, Y21, U27 		_	_	
OV _{DD}	V16, W11, W14, Y18, AA13, AA21, AB11, AB17, AB24, AC4, AC9, AC21, AD6, AD13, AD17, AD19, AE10, AE8, AE24, AF4, AF12, AF22, AF27, AG26	Power for PCI and other standards (3.3 V)	OV _{DD}	—	

Package Description

Table 72	. MPC8547E	Pinout Listing	(continued)
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Signal	Package Pin Number	Pin Type	Power Supply	Notes
Reserved	AE26	_		2
cfg_pci1_clk	AG24	I	OV _{DD}	5
Reserved	AF25	_		101
Reserved	AE25	_	_	2
Reserved	AG25	_	_	2
Reserved	AD24	_	_	2
Reserved	AF24	_		2
Reserved	AD27	_		2
Reserved	AD28, AE27, W17, AF26	_		2
Reserved	AH25	_		2
	DDR SDRAM Memory Interface			
MDQ[0:63]	L18, J18, K14, L13, L19, M18, L15, L14, A17, B17, A13, B12, C18, B18, B13, A12, H18, F18, J14, F15, K19, J19, H16, K15, D17, G16, K13, D14, D18, F17, F14, E14, A7, A6, D5, A4, C8, D7, B5, B4, A2, B1, D1, E4, A3, B2, D2, E3, F3, G4, J5, K5, F6, G5, J6, K4, J1, K2, M5, M3, J3, J2, L1, M6	I/O	GV _{DD}	_
MECC[0:7]	H13, F13, F11, C11, J13, G13, D12, M12	I/O	GV _{DD}	—
MDM[0:8]	M17, C16, K17, E16, B6, C4, H4, K1, E13	0	GV _{DD}	—
MDQS[0:8]	M15, A16, G17, G14, A5, D3, H1, L2, C13	I/O	GV _{DD}	—
MDQS[0:8]	L17, B16, J16, H14, C6, C2, H3, L4, D13	I/O	GV _{DD}	—
MA[0:15]	A8, F9, D9, B9, A9, L10, M10, H10, K10, G10, B8, E10, B10, G6, A10, L11	0	GV _{DD}	_
MBA[0:2]	F7, J7, M11	0	GV _{DD}	—
MWE	E7	0	GV _{DD}	—
MCAS	H7	0	GV _{DD}	—
MRAS	L8	0	GV _{DD}	—
MCKE[0:3]	F10, C10, J11, H11	0	GV _{DD}	11
MCS[0:3]	K8, J8, G8, F8	0	GV _{DD}	—
MCK[0:5]	H9, B15, G2, M9, A14, F1	0	GV _{DD}	—
MCK[0:5]	J9, A15, G1, L9, B14, F2	0	GV _{DD}	_
MODT[0:3]	E6, K6, L7, M7	0	GV _{DD}	_
MDIC[0:1]	A19, B19	I/O	GV _{DD}	36

Package Description

Signal	Package Pin Number	Pin Type	Power Supply	Notes
GV _{DD}	B3, B11, C7, C9, C14, C17, D4, D6, D10, D15, E2, E8, E11, E18, F5, F12, F16, G3, G7, G9, G11, H5, H12, H15, H17, J10, K3, K12, K16, K18, L6, M4, M8, M13	Power for DDR1 and DDR2 DRAM I/O voltage (1.8 V, 2.5 V)	GV _{DD}	
BV _{DD}	C21, C24, C27, E20, E25, G19, G23, H26, J20	Power for local bus (1.8 V, 2.5 V, 3.3 V)	BV _{DD}	_
V _{DD}	M19, N12, N14, N16, N18, P11, P13, P15, P17, P19, R12, R14, R16, R18, T11, T13, T15, T17, T19, U12, U14, U16, U18, V17, V19	Power for core (1.1 V)	V _{DD}	_
SV _{DD}	L25, L27, M24, N28, P24, P26, R24, R27, T25, V24, V26, W24, W27, Y25, AA28, AC27	Core power for SerDes transceivers (1.1 V)	SV _{DD}	_
XV _{DD}	L20, L22, N23, P21, R22, T20, U23, V21, W22, Y20	Pad power for SerDes transceivers (1.1 V)	XV _{DD}	_
AVDD_LBIU	J28	Power for local bus PLL (1.1 V)	_	26
AVDD_PCI1	AH21	Power for PCI1 PLL (1.1 V)	_	26
AVDD_PCI2	AH22	Power for PCI2 PLL (1.1 V)		26
AVDD_CORE	AH15	Power for e500 PLL (1.1 V)		26
AVDD_PLAT	AH19	Power for CCB PLL (1.1 V)		26
AVDD_SRDS	U25	Power for SRDSPLL (1.1 V)		26
SENSEVDD	M14	0	V _{DD}	13
SENSEVSS	M16	—	_	13
	Analog Signals			
MVREF	A18	I Reference voltage signal for DDR	MVREF	

Table 73. MPC8545E Pinout Listing (continued)

Package Description

Signal	Package Pin Number	Pin Type	Power Supply	Notes
PCI1_TRDY	AG11	I/O	OV _{DD}	2
PCI1_REQ[4:1]	AH2, AG4, AG3, AH4	ļ	OV _{DD}	—
PCI1_REQ0	AH3	I/O	OV _{DD}	—
PCI1_CLK	AH26	I	OV _{DD}	39
PCI1_DEVSEL	AH11	I/O	OV _{DD}	2
PCI1_FRAME	AE11	I/O	OV _{DD}	2
PCI1_IDSEL	AG9	I	OV _{DD}	—
cfg_pci1_width	AF14	I/O	OV _{DD}	112
Reserved	V15	_	_	110
Reserved	AE28	_	_	2
Reserved	AD26	_	_	110
Reserved	AD25	_	_	110
Reserved	AE26	_	_	110
cfg_pci1_clk	AG24	I	OV _{DD}	5
Reserved	AF25	_	_	101
Reserved	AE25	_	_	110
Reserved	AG25	_	_	110
Reserved	AD24	_	_	110
Reserved	AF24	_	_	110
Reserved	AD27	_	_	110
Reserved	AD28, AE27, W17, AF26	_	_	110
Reserved	AH25	_	_	110
	DDR SDRAM Memory Interface			
MDQ[0:63]	L18, J18, K14, L13, L19, M18, L15, L14, A17, B17, A13, B12, C18, B18, B13, A12, H18, F18, J14, F15, K19, J19, H16, K15, D17, G16, K13, D14, D18, F17, F14, E14, A7, A6, D5, A4, C8, D7, B5, B4, A2, B1, D1, E4, A3, B2, D2, E3, F3, G4, J5, K5, F6, G5, J6, K4, J1, K2, M5, M3, J3, J2, L1, M6	I/O	GV _{DD}	_
MECC[0:7]	H13, F13, F11, C11, J13, G13, D12, M12	I/O	GV _{DD}	—
MDM[0:8]	M17, C16, K17, E16, B6, C4, H4, K1, E13	0	GV _{DD}	
MDQS[0:8]	M15, A16, G17, G14, A5, D3, H1, L2, C13	I/O	GV _{DD}	_
MDQS[0:8]	L17, B16, J16, H14, C6, C2, H3, L4, D13	I/O	GV _{DD}	
MA[0:15]	A8, F9, D9, B9, A9, L10, M10, H10, K10, G10, B8, E10, B10, G6, A10, L11	0	GV _{DD}	—
MBA[0:2]	F7, J7, M11	0	GV _{DD}	_

Table 74. MPC8543E Pinout Listing (continued)

- First, the board must have at least 10 × 10-nF SMT ceramic chip capacitors as close as possible to the supply balls of the device. Where the board has blind vias, these capacitors must be placed directly below the chip supply and ground connections. Where the board does not have blind vias, these capacitors must be placed in a ring around the device as close to the supply and ground connections as possible.
- Second, there must be a $1-\mu F$ ceramic chip capacitor from each SerDes supply (SV_{DD} and XV_{DD}) to the board ground plane on each side of the device. This must be done for all SerDes supplies.
- Third, between the device and any SerDes voltage regulator there must be a 10- μ F, low equivalent series resistance (ESR) SMT tantalum chip capacitor and a 100- μ F, low ESR SMT tantalum chip capacitor. This must be done for all SerDes supplies.

22.5 Connection Recommendations

To ensure reliable operation, it is highly recommended to connect unused inputs to an appropriate signal level. All unused active low inputs must be tied to V_{DD} , TV_{DD} , BV_{DD} , OV_{DD} , GV_{DD} , and LV_{DD} , as required. All unused active high inputs must be connected to GND. All NC (no-connect) signals must remain unconnected. Power and ground connections must be made to all external V_{DD} , TV_{DD} , BV_{DD} , OV_{DD} , GV_{DD} , TV_{DD} , BV_{DD} , OV_{DD} , GV_{DD} , LV_{DD} , and GND pins of the device.

22.6 Pull-Up and Pull-Down Resistor Requirements

The device requires weak pull-up resistors (2–10 k Ω is recommended) on open drain type pins including I²C pins and PIC (interrupt) pins.

Correct operation of the JTAG interface requires configuration of a group of system control pins as demonstrated in Figure 63. Care must be taken to ensure that these pins are maintained at a valid deasserted state under normal operating conditions as most have asynchronous behavior and spurious assertion gives unpredictable results.

The following pins must not be pulled down during power-on reset: TSEC3_TXD[3], HRESET_REQ, TRIG_OUT/READY/QUIESCE, MSRCID[2:4], ASLEEP. The DMA_DACK[0:1], and TEST_SEL/TEST_SEL pins must be set to a proper state during POR configuration. See the pinlist table of the individual device for more details

See the PCI 2.2 specification for all pull ups required for PCI.

22.7 Output Buffer DC Impedance

The device drivers are characterized over process, voltage, and temperature. For all buses, the driver is a push-pull single-ended driver type (open drain for I^2C).

To measure Z_0 for the single-ended drivers, an external resistor is connected from the chip pad to OV_{DD} or GND. Then, the value of each resistor is varied until the pad voltage is $OV_{DD}/2$ (see Figure 61). The output impedance is the average of two components, the resistances of the pull-up and pull-down devices. When data is held high, SW1 is closed (SW2 is open) and R_P is trimmed until the voltage at the pad equals $OV_{DD}/2$. R_P then becomes the resistance of the pull-up devices. R_P and R_N are designed to be close to each other in value. Then, $Z_0 = (R_P + R_N)/2$.

System Design Information



Figure 61. Driver Impedance Measurement

This table summarizes the signal impedance targets. The driver impedances are targeted at minimum V_{DD} , nominal OV_{DD} , 105°C.

Table 86. Impedance Characteristics

Impedance	Local Bus, Ethernet, DUART, Control, Configuration, Power Management	PCI	DDR DRAM	Symbol	Unit
R _N	43 Target	25 Target	20 Target	Z ₀	W
R _P	43 Target	25 Target	20 Target	Z ₀	W

Note: Nominal supply voltages. See Table 1, $T_i = 105^{\circ}C$.

22.8 Configuration Pin Muxing

The device provides the user with power-on configuration options which can be set through the use of external pull-up or pull-down resistors of $4.7 \text{ k}\Omega$ on certain output pins (see customer visible configuration pins). These pins are generally used as output only pins in normal operation.

While $\overline{\text{HRESET}}$ is asserted however, these pins are treated as inputs. The value presented on these pins while $\overline{\text{HRESET}}$ is asserted, is latched when $\overline{\text{HRESET}}$ deasserts, at which time the input receiver is disabled and the I/O circuit takes on its normal function. Most of these sampled configuration pins are equipped with an on-chip gated resistor of approximately 20 k Ω . This value must permit the 4.7-k Ω resistor to pull the configuration pin to a valid logic low level. The pull-up resistor is enabled only during $\overline{\text{HRESET}}$ (and for platform/system clocks after $\overline{\text{HRESET}}$ deassertion to ensure capture of the reset value). When the input receiver is disabled the pull-up is also, thus allowing functional operation of the pin as an output with minimal signal quality or delay disruption. The default value for all configuration bits treated this way has been encoded such that a high voltage level puts the device into the default state and external resistors are needed only when non-default settings are required by the user.

Careful board layout with stubless connections to these pull-down resistors coupled with the large value of the pull-down resistor minimizes the disruption of signal quality or speed for output pins thus configured.

System Design Information



Notes:

- 1. The COP port and target board must be able to independently assert HRESET and TRST to the processor in order to fully control the processor as shown here.
- 2. Populate this with a 10– $\!\Omega$ resistor for short-circuit/current-limiting protection.
- 3. The KEY location (pin 14) is not physically present on the COP header.
- 4. Although pin 12 is defined as a No-Connect, some debug tools may use pin 12 as an additional GND pin for improved signal integrity.
- This switch is included as a precaution for BSDL testing. The switch must be closed to position A during BSDL testing to avoid accidentally asserting the TRST line. If BSDL testing is not being performed, this switch must be closed to position B.
- 6. Asserting SRESET causes a machine check interrupt to the e500 core.

Figure 63. JTAG Interface Connection